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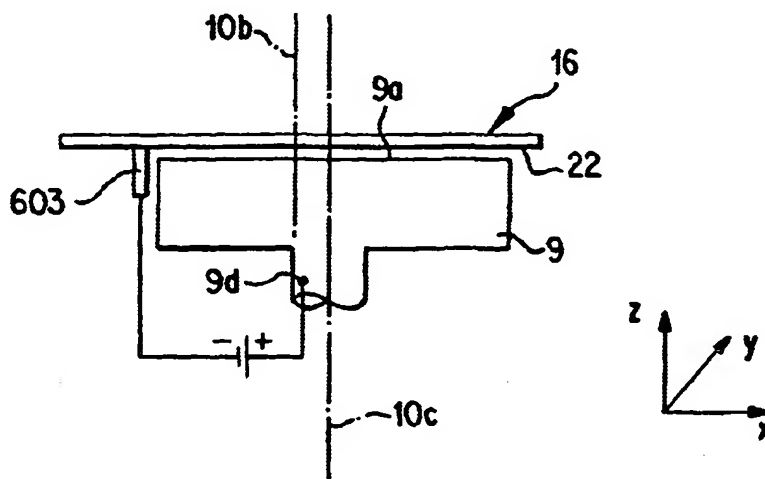
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(54) Title: METHOD OF AND APPARATUS FOR MAKING ELECTRICAL CONTACT TO WAFER SURFACE FOR FULL-FACE ELECTROPLATING OR ELECTROPOLISHING



(57) **Abstract:** Deposition of conductive material on or removal of conductive material from a wafer frontal side of a semiconductor wafer is performed by providing an anode having an anode area which is to face the wafer frontal side, and electrically connecting the wafer frontal side with at least one electrical contact, outside of the anode area, by pushing the electrical contact and the wafer frontal side into proximity with each other. A potential is applied between the anode and the electrical contact, and the wafer is moved with respect to the anode and the electrical contact. Full-face electroplating or electropolishing over the wafer frontal side surface, in its entirety, is thus permitted.

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